



Case Docket No. SEPP21.001C1
Date: February 3, 2004

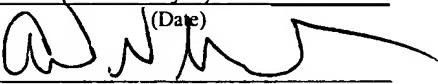
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Tois et al.
App. No. : 10/678,766
Filed : October 2, 2003
For : METHOD OF GROWING
OXIDE THIN FILMS
Examiner : Unknown
Group Art Unit : 1765

I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on

February 3, 2004

(Date)


Andrew N. Merickel, Reg. No. 53,317

TRANSMITTAL LETTER

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed for filing in the above-identified application are:

- (X) An Information Disclosure Statement.
- (X) A PTO Form 1449 listing seventeen (17) references that are not enclosed.
- (X) The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment, to Account No. 11-1410.
- (X) Return prepaid postcard.



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INFORMATION DISCLOSURE STATEMENT

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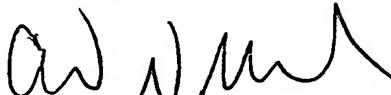
Enclosed is form PTO-1449 listing 17 references that are of record in U.S. patent application No. 10/148,525, filed August 27, 2002, which is the parent of this continuation application, and is relied upon for an earlier filing date under 35 U.S.C. § 120. Copies of the references are not submitted pursuant to 37 C.F.R. § 1.98(d).

This Information Disclosure Statement is being filed before the receipt of a first Office Action on the merits, and presumably no fee is required in accordance with 37 C.F.R. § 1.97(b)(3). If a first Office Action on the merits was mailed before the mailing date of this Statement, the Commissioner is authorized to charge the fee set forth in 37 C.F.R. § 1.17(p) to Deposit Account No. 11-1410.

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: February 3, 2004

By: 

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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. SEPP21.001C	APPLICATION NO. 10/678,766
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		FEB 8 9 2004 U.S. PATENT & TRADEMARK OFFICE JC42 24	
(USE SEVERAL SHEETS IF NECESSARY)		APPLICANT TOIS et al.	
		FILING DATE October 2, 2003	GROUP 1765

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
1.	5,480,818	01/02/96	Matsumoto et al.	437	40	02/09/93
2.	6,006,763	12/28/99	Mori et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
3.	JP 3286531 A2	12.17.91	Japan Abstract				
4.	JP 60065712 A2	04.15.85	Japan Abstract				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
5	Klaus, J. W. et al., "Atomic Layer Deposition of SiO ₂ Using Catalyzed and Uncatalyzed Self-Limiting Surface Reactions," <u>Surface Review and Letters</u> , Vol. 6, Nos. 3 & 4, pp. 435-448 (1999).	
6	Niinistö, L. et al., "Synthesis of oxide thin films and overlayers by atomic layer epitaxy for advanced applications," <u>Materials Science and Engineering</u> , B41, pp. 23-29 (1996).	
7	Wise, M. L. et al., "Diethyldiethoxysilane as a New Precursor for SiO ₂ Growth on Silicon," <u>Mat. Res. Soc. Symp. Proc.</u> , Vol. 334, pp. 37-43 (1994).	
8	Yamaguchi, Kei-ichi et al., "Atomic-layer chemical-vapor-deposition of silicon dioxide films with an extremely low hydrogen content," <u>Appl. Surf. Science</u> , 130-132; pp. 202-207 (1998)	
9	George, S.M., et al., "Surface Chemistry for Atomic Layer Growth," <u>J. Phys. Chem.</u> , 100:13121-13131 (1996)	
10	George, S.M. et al., "Atomic layer controlled deposition of SiO ₂ and Al ₂ O ₃ using ABAB... binary reaction sequence chemistry," <u>Appl. Surf. Science</u> , 82/83:460-467 (1994)	
11	Jeon, H., "A Study on the Characteristics of TiN Thin Film Deposited by Atomic Layer Chemical Vapor Deposition Method," <u>AVS 46th International Symposium</u> , Seattle, WA, abstract TF-MoP17 (1999)	
12	Jeon, H., et al., "A Study on the Characteristics of TiN Thin Film Deposited by Atomic Layer Chemical Vapor Deposition Method," <u>J. Vac. Sci. Technol. A</u> , 18(4), 1595-1598 (2000)	
13	Klaus, J.W., et al., "Atomically controlled growth of tungsten and tungsten nitride using sequential surface reactions," <u>Appl. Surf. Science</u> 162-163; 479-471 (2000)	
14	Klaus, J.W., et al., "Atomic layer deposition of tungsten nitride films using sequential surface reactions," <u>Journal of the Electrochemical Soc.</u> , 147 (3):1175-1181 (2000)	
15	Klaus, J.W. et al., "Atomic layer deposition of tungsten using sequential surface chemistry with a sacrificial stripping reaction," <u>Thin Solid Films</u> , 360:145-153 (2000)	
16	Klaus, J.W., et al., "Atomic layer deposition of tungsten and tungsten nitride using sequential surface reactions," <u>AVS 46th International Symposium</u> , Seattle, WA, abstract TF-TuM6 (1999)	
17	Riihelä, D. et al., "Introducing atomic layer epitaxy for the deposition of optical thin films," <u>Thin Solid Films</u> , Vol. 289, pp. 250-255 (1996).	

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EXAMINER	DATE CONSIDERED
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	